

GSM4874WS

60V N-Channel Enhancement Mode MOSFET

Product Description

GSM4874WS, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

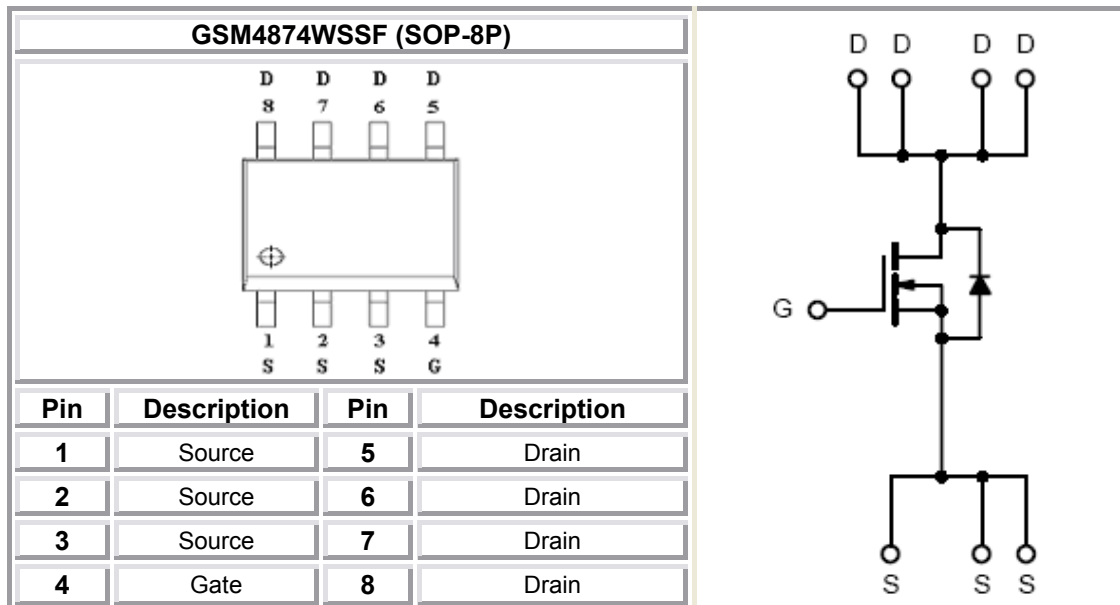
Features

- 60V/12A, $R_{DS(ON)}=11m\Omega@V_{GS}=10V$
- 60V/10A, $R_{DS(ON)}=15m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- SOP-8P package design

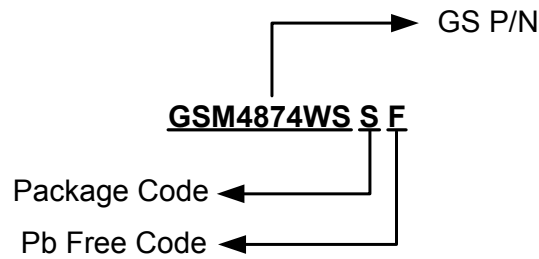
Applications

- Motor and Load Control
- Power Management in White LED System
- Push Pull Converter
- LCD TV Inverter & AD/DC Inverter Systems.

Packages & Pin Assignments

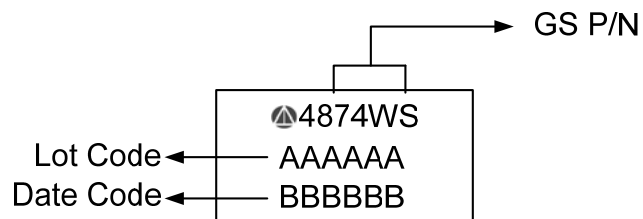


Ordering Information



Part Number	Package	Quantity Reel
GSM4874WSSF	SOP-8P	3000 PCS

Marking Information



Absolute Maximum Ratings

(T_A=25°C unless otherwise noted)

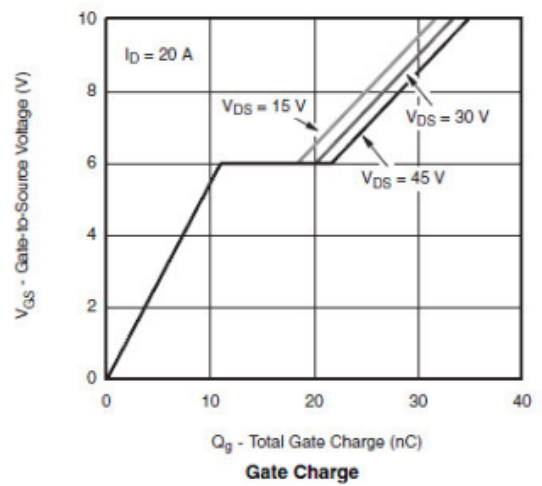
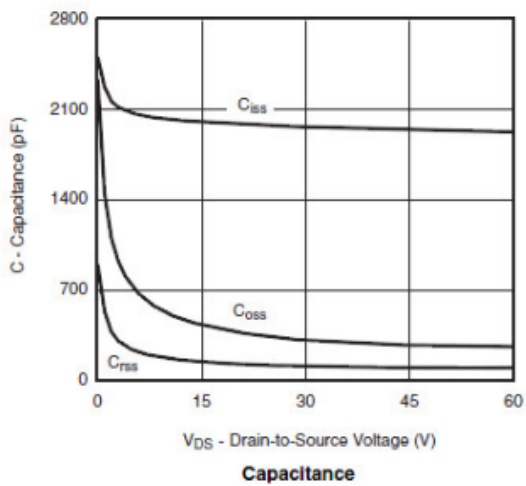
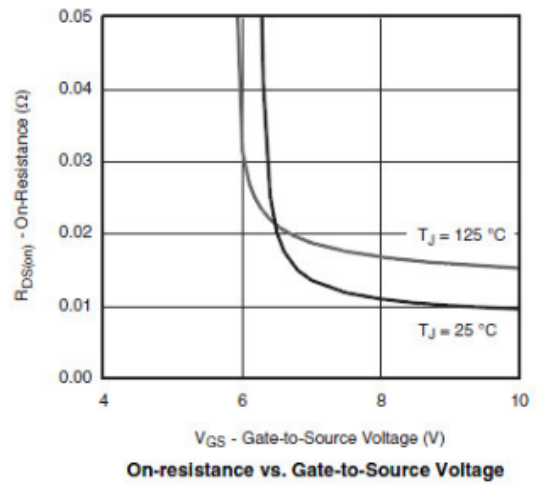
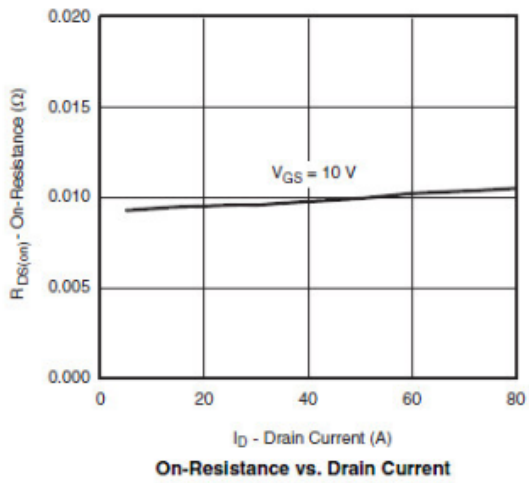
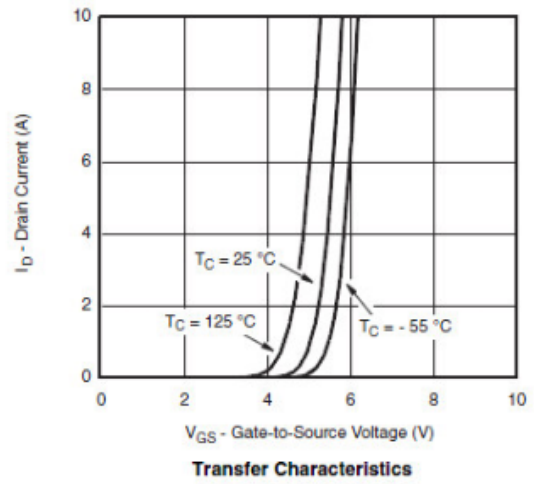
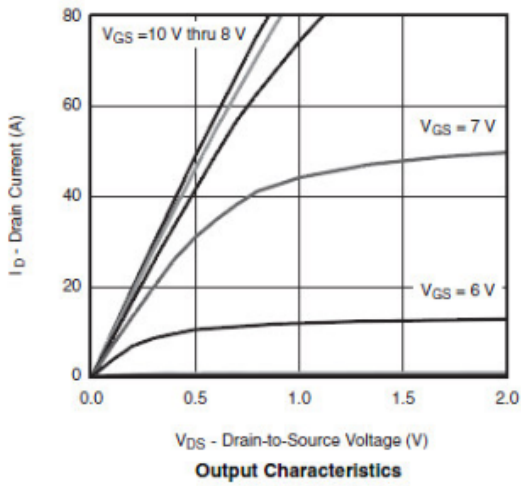
Symbol	Parameter	Typical	Unit	
V _{DSS}	Drain-Source Voltage	60	V	
V _{GSS}	Gate -Source Voltage	±20	V	
I _D	Continuous Drain Current(T _J =150°C)	T _A =25°C	12	A
		T _A =70°C	10	
I _{DM}	Pulsed Drain Current	40	A	
I _S	Continuous Source Current(Diode Conduction)	1.5	A	
P _D	Power Dissipation	T _A =25°C	2.8	W
		T _A =70°C	1.8	
T _J	Operating Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-55/150	°C	
R _{θJA}	Thermal Resistance-Junction to Ambient	62.5	°C/ W	

Electrical Characteristics

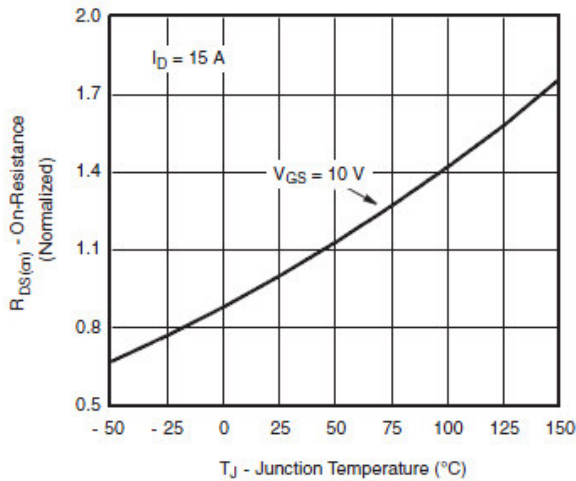
($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	
I_{GSS}	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=48V, V_{GS}=0V$			1	uA
		$V_{DS}=48V, V_{GS}=0V, T_J=85^\circ\text{C}$			30	
$I_{D(on)}$	On-State Drain Current	$V_{DS}\geq 10V, V_{GS}=10V$	40			A
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=12A$		8	11	m Ω
		$V_{GS}=4.5V, I_D=10A$		12	15	
g_{FS}	Forward Transconductance	$V_{DS}=15V, I_D=10A$		38		S
V_{SD}	Diode Forward Voltage	$I_S=10A, V_{GS}=0V$		0.8	1.3	V
Dynamic						
C_{iss}	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, f=1\text{MHz}$		2080		pF
C_{oss}	Output Capacitance			320		
C_{rss}	Reverse Transfer Capacitance			120		
Q_g	Total Gate Charge	$V_{DS}=30V, V_{GS}=10V, I_D=10A$		35	60	nC
Q_{gs}	Gate-Source Charge			12		
Q_{gd}	Gate-Drain Charge			10		
$t_{d(on)}$	Turn-On Time	$V_{DD}=30V, R_L=1.53\Omega, I_D=10A, V_{GEN}=10V, R_G=1.0\Omega$		10	20	ns
t_r				10	20	
$t_{d(off)}$	Turn-Off Time			15	30	
t_f				10	20	

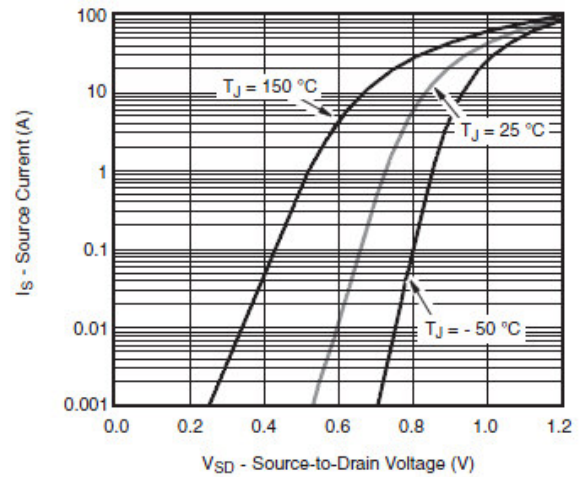
Typical Performance Characteristics



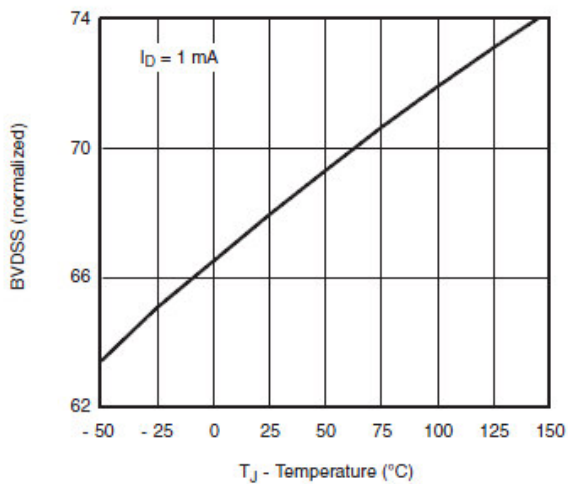
Typical Performance Characteristics (continue)



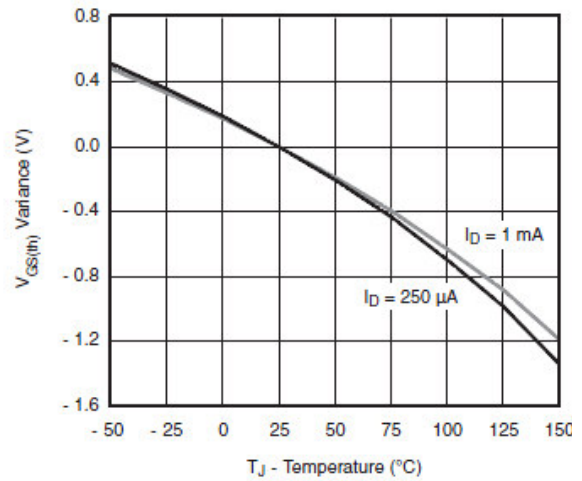
On-Resistance vs. Junction Temperature



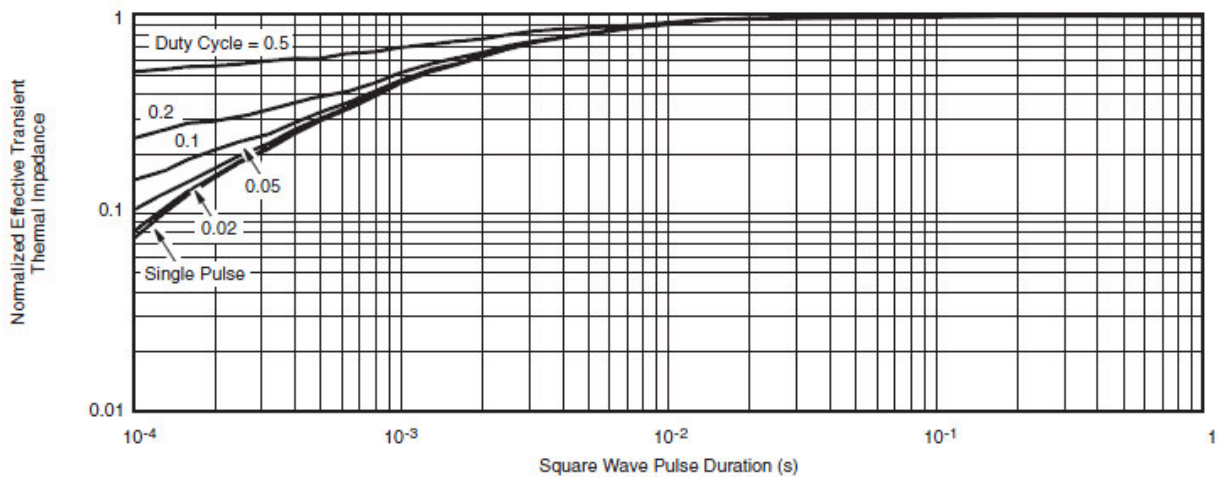
Source-Drain Diode Forward Voltage



Drain-Source Breakdown vs. Junction Temperature



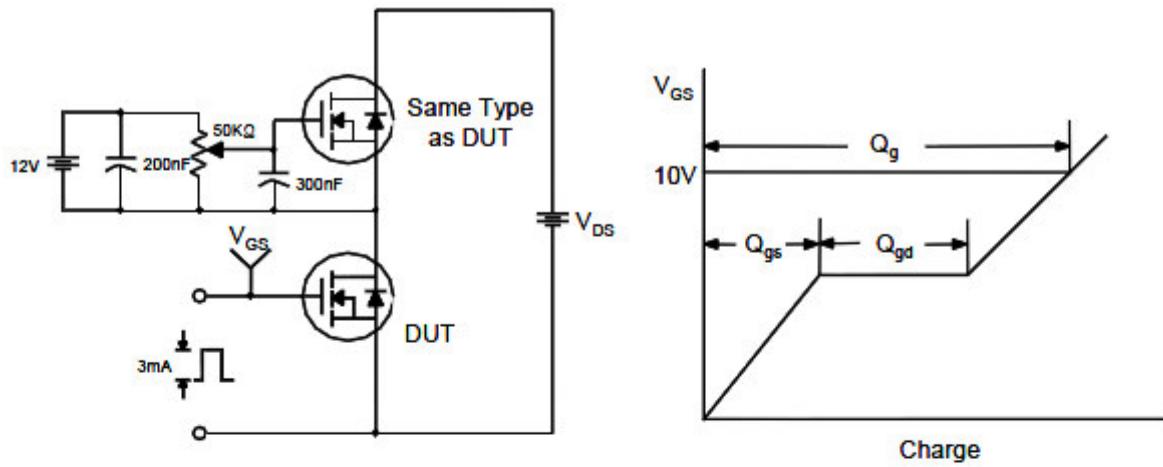
Threshold Voltage



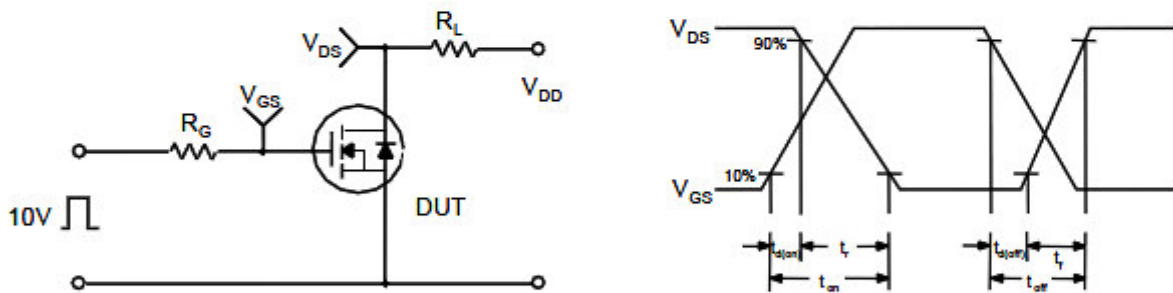
Normalized Thermal Transient Impedance, Junction-to-Case

Typical Characteristics

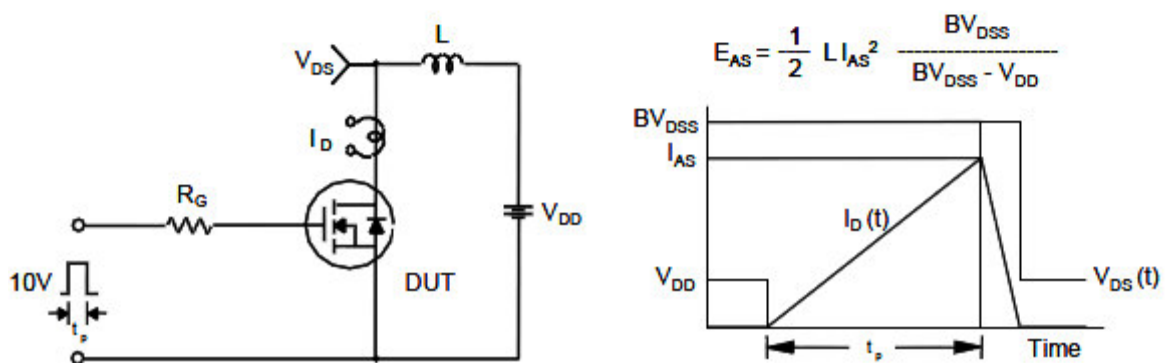
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

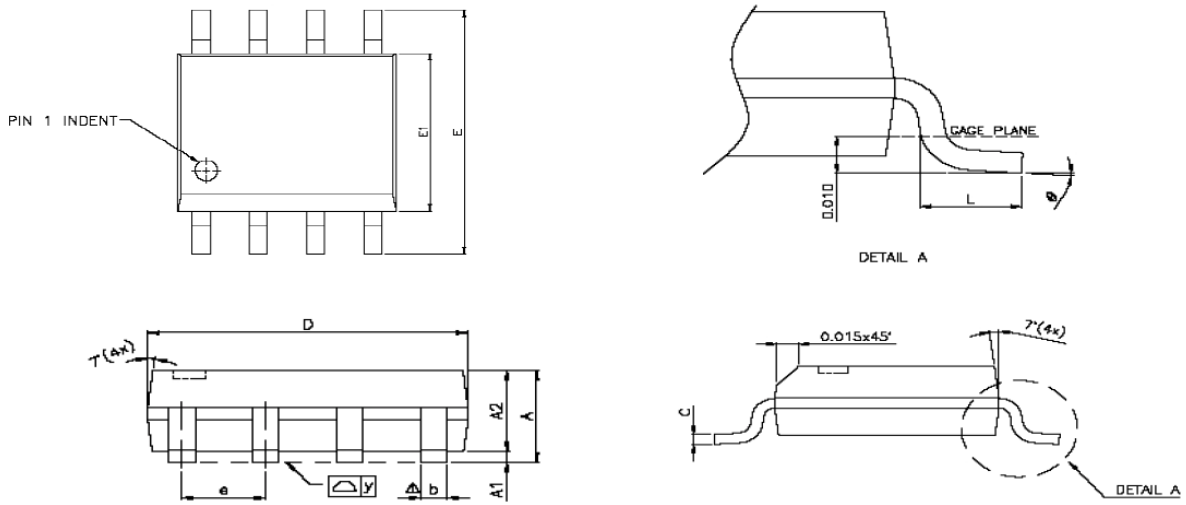


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

SOP-8P







Dimensions





Symbol	Millimeters			Inches		
	Min	Nom	Max	Min	Nom	Max
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	-	0.25	0.004	-	0.010
A2	-	1.45	-	-	0.057	-
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	-	1.27	-	-	0.050	-
L	0.38	0.71	1.27	0.015	0.028	0.050
Δy	-	-	0.076	-	-	0.003
θ	0°	-	8°	0°	-	8°



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